

TOSHIBA HIGH EFFICIENCY RECTIFIER (HED) SILICON EPITAXIAL JUNCTION TYPE

# 1DL41A

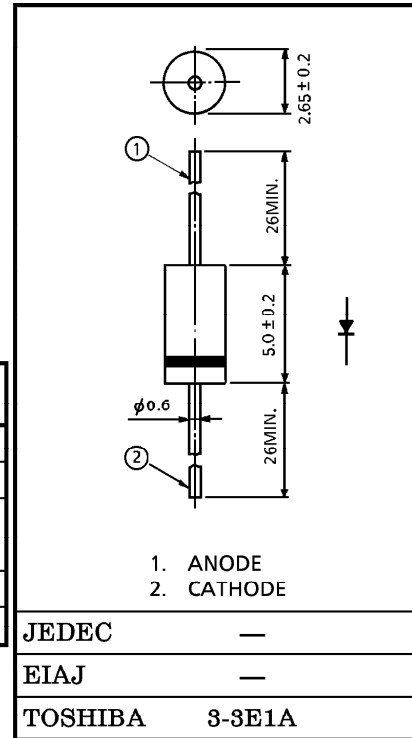
SWITCHING TYPE POWER SUPPLY APPLICATIONS

Unit in mm

- Repetitive Peak Reverse Voltage :  $V_{RRM}=200V$
- Average Forward Current :  $I_F(AV)=1.0A$  ( $T_a=64^\circ C$ )
- Very Fast Reverse-Recovery Time :  $t_{rr}=35ns$  (Max.)
- Low Forward Voltage :  $V_{FM}=0.98V$  (Max.)
- Available to Reduce Switching Losses and Output Noise.

**MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	$V_{RRM}$	200	V
Average Forward Current	$I_F(AV)$	1.0	A
Peak One Cycle Surge Forward Current (Non-Repetitive)	$I_{FSM}$	30 (50Hz)	A
		33 (60Hz)	
Junction Temperature	$T_j$	-40~150	°C
Storage Temperature Range	$T_{stg}$	-40~150	°C

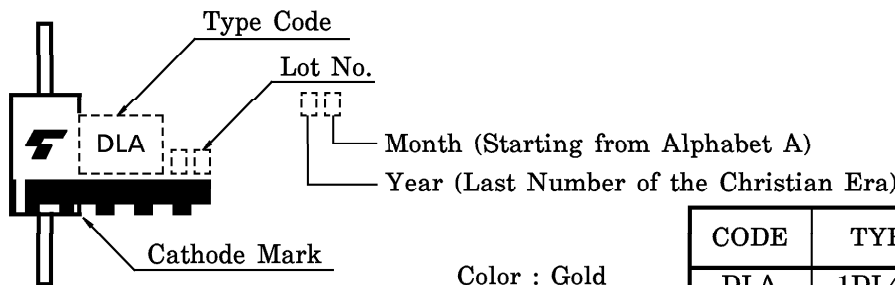


Weight : 0.225g

**ELECTRICAL CHARACTERISTICS** ( $T_a = 25^\circ C$ )

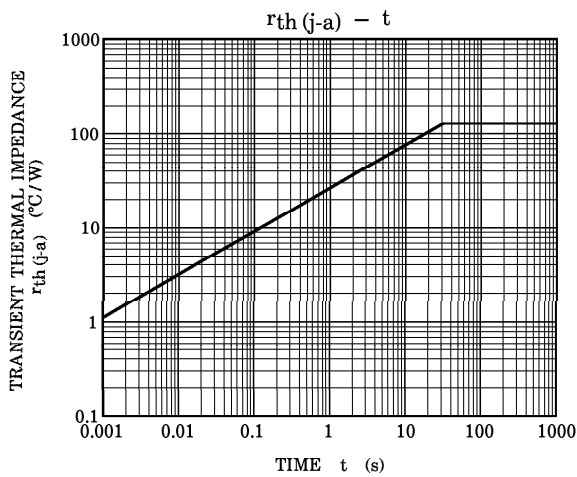
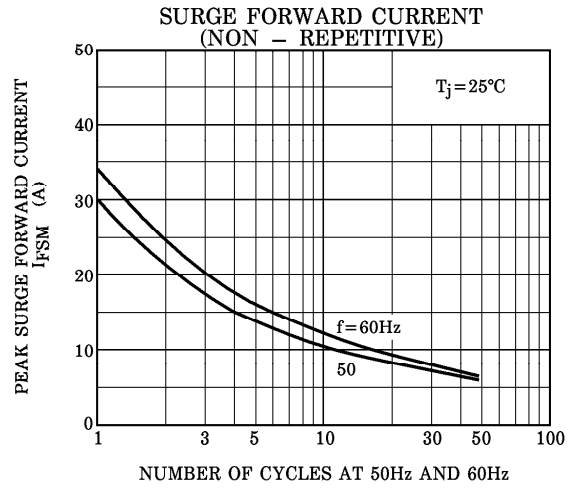
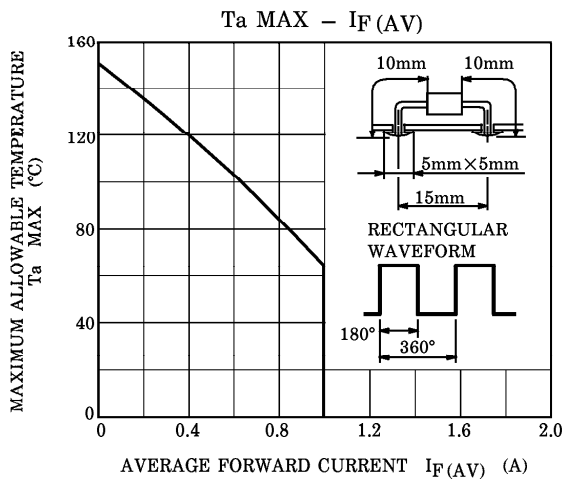
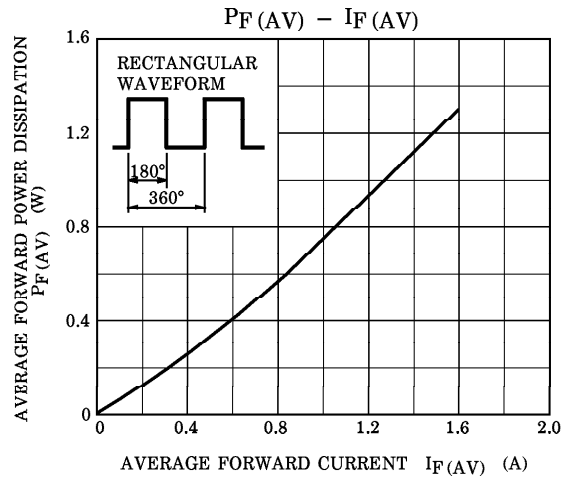
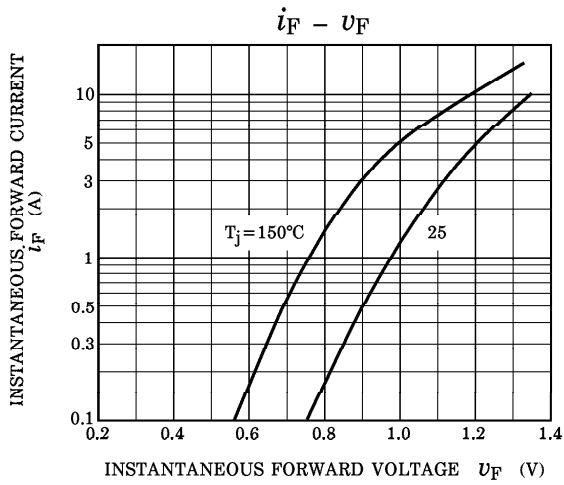
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	$V_{FM}$	$I_{FM}=1.0A$	—	—	0.98	V
Repetitive Peak Reverse Current	$I_{RRM}$	$V_{RRM}=200V$	—	—	100	$\mu A$
Reverse Recovery Time	$t_{rr}$	$I_F=1A, di/dt=-30A/\mu s$	—	—	35	ns
Forward Recovery Time	$t_{fr}$	$I_F=1.0A$	—	—	100	ns
Thermal Resistance	$R_{th(j-a)}$	Junction to Ambient	—	—	115	°C/W
Thermal Resistance	$R_{th(j-l)}$	Junction to Lead	—	—	45	°C/W

**MARKING**



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